



# SPN8622

## Dual N-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPN8622 is a dual N-Channel logic enhancement mode power field effect transistor which is produced using super high cell density DMOS trench technology. The SPN8622 has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

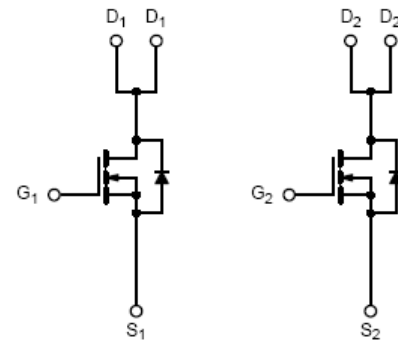
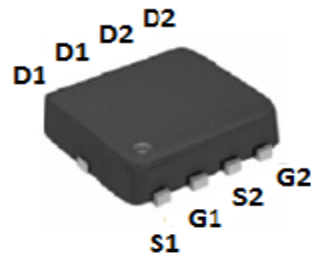
### FEATURES

- ◆ 20V/5A,  $R_{DS(ON)}=14m\Omega@V_{GS}=4.5V$
- ◆ 20V/4A,  $R_{DS(ON)}=18m\Omega@V_{GS}=2.5V$
- ◆ 20V/4A,  $R_{DS(ON)}=28m\Omega@V_{GS}=1.8V$
- ◆ High density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ PPAK3x3-8L\* package design

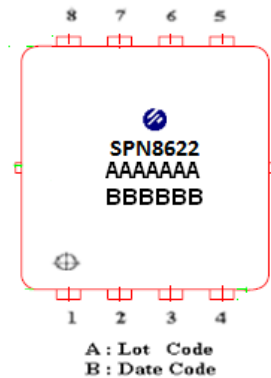
### APPLICATIONS

- Powered System
- DC/DC Converter
- Load Switch

### PIN CONFIGURATION (PPAK3x3-Dual 8L)



### PART MARKING





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### PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source
2	G1	Gate
3	S2	Source
4	G2	Gate
5	D2	Drain
6	D2	Drain
7	D1	Drain
8	D1	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPN8622DN8RGB	PPAK3x3-Dual 8L	SPN8622

※ SPN8622DN8RGB : Tape Reel ; Pb – Free ; Halogen - Free

### ABSOLUTE MAXIMUM RATINGS

( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	$V_{DSS}$	20	V
Gate –Source Voltage	$V_{GSS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	20	A
Continuous Drain Current		23	
Pulsed Drain Current	$I_{DM}$	39	A
Power Dissipation @ $T_C=25^{\circ}\text{C}$	$P_D$	26	W
Operating Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-55/150	$^{\circ}\text{C}$
Thermal Resistance-Junction to Ambient	$R_{\theta JC}$	4.8	$^{\circ}\text{C}/\text{W}$

\*Limited by the package.



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### ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5		1	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=16V, V_{GS}=0V$			1	uA
		$V_{DS}=16V, V_{GS}=0V$ $T_J=55^\circ C$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\geq 5V, V_{GS}=10V$	20			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=5A$			14	mΩ
		$V_{GS}=2.5V, I_D=4A$			18	mΩ
		$V_{GS}=1.8V, I_D=4A$			28	mΩ
Forward Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=15A$		24		S
Gate resistance	$R_g$	$f=1MHz$		1.4		Ω
Diode Forward Voltage	$V_{SD}$	$I_S=1A, V_{GS}=0V$			1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=15V, V_{GS}=4.5V$ $I_D=5A$		10.1		nC
Gate-Source Charge	$Q_{gs}$			1.2		
Gate-Drain Charge	$Q_{gd}$			3.4		
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V$ $f=1MHz$		702		pF
Output Capacitance	$C_{oss}$			97		
Reverse Transfer Capacitance	$C_{rss}$			96		
Turn-On Time	$t_{d(on)}$	$V_{DD}=15V, I_D=5A,$ $V_{GS}=4.5V, R_G=3.3\Omega$		6		nS
	$t_r$			41		
Turn-Off Time	$t_{d(off)}$			17		
	$t_f$			7		



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### TYPICAL CHARACTERISTICS

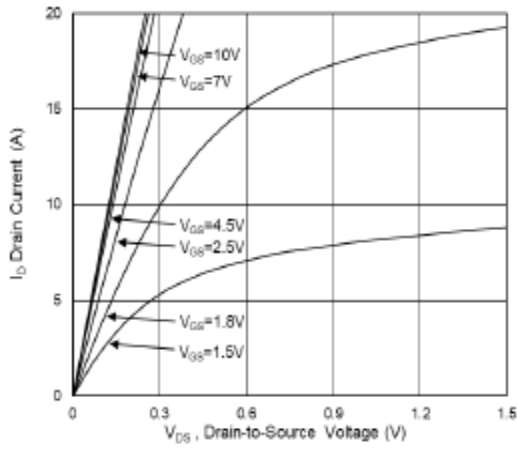


Fig.1 Typical Output Characteristics

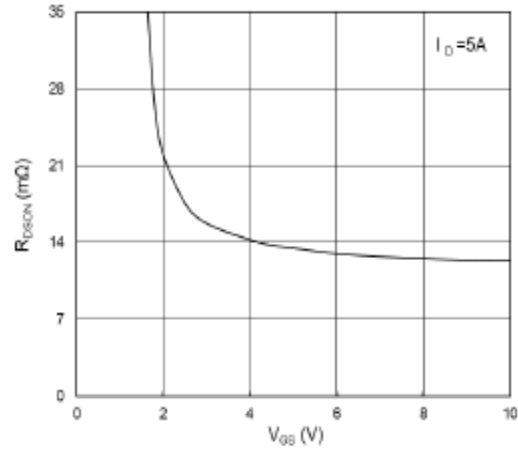


Fig.2 On-Resistance vs G-S Voltage

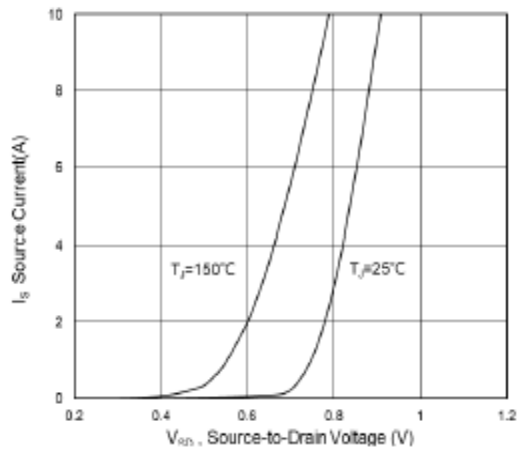


Fig.3 Source Drain Forward Characteristics

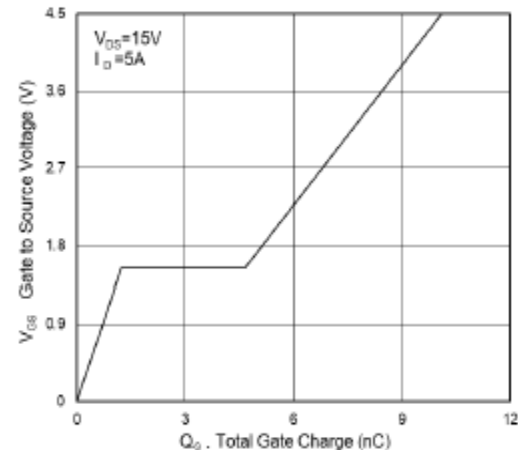


Fig.4 Gate-Charge Characteristics

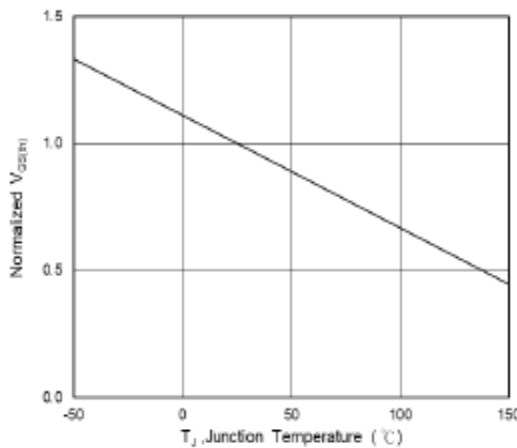


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$

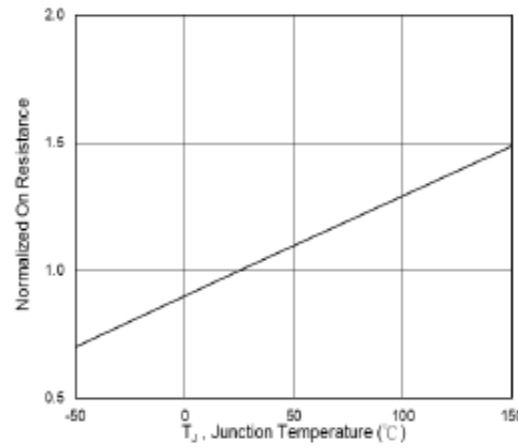


Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$



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### TYPICAL CHARACTERISTICS

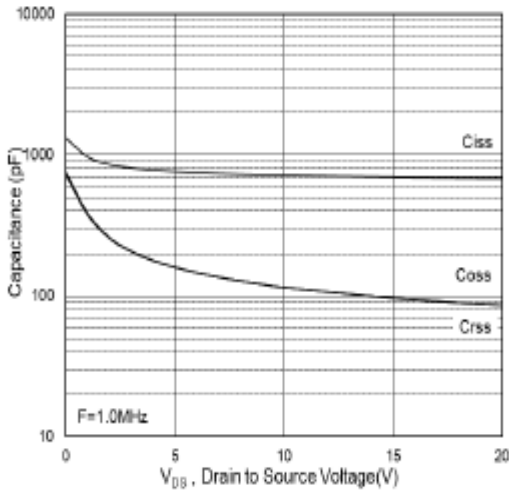


Fig.7 Capacitance

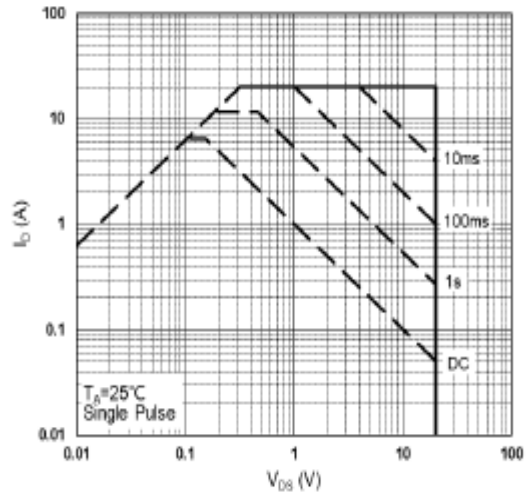


Fig.8 Safe Operating Area

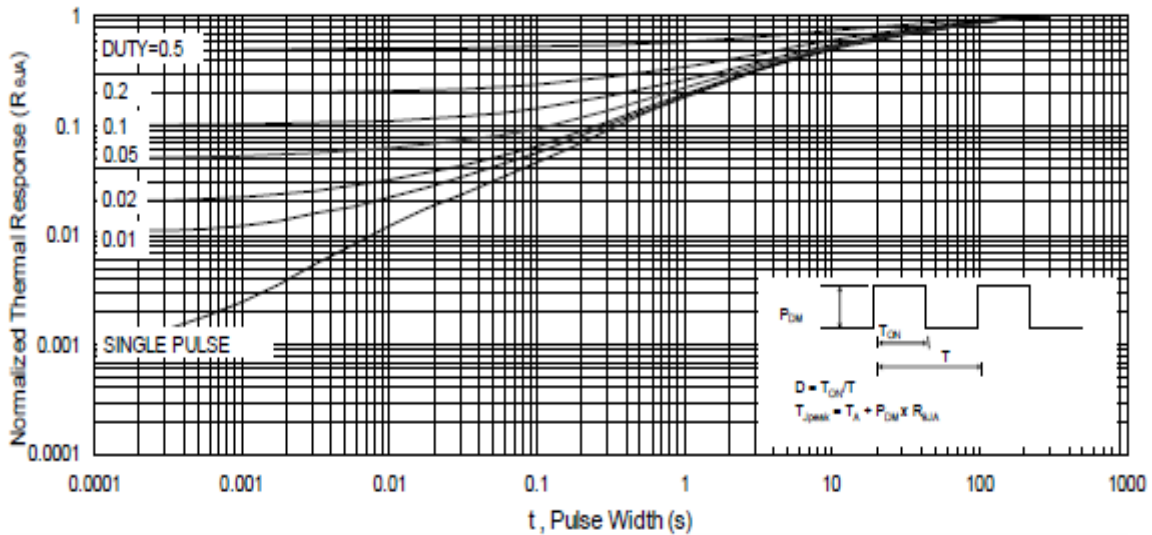


Fig.9 Normalized Maximum Transient Thermal Impedance



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